

FDG6303N Dual N-Channel, Digital FET

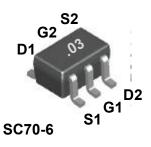
General Description

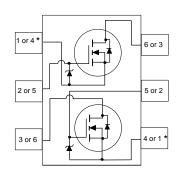
These dual N-Channel logic level enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs.

Features

- $\begin{tabular}{ll} \blacksquare & 25 \ V, \ 0.50 \ A \ continuous, \ 1.5 \ A \ peak. \\ & R_{\rm DS(ON)} = 0.45 \ \Omega \ @ \ V_{\rm GS} = 4.5 \ V, \\ & R_{\rm DS(ON)} = 0.60 \ \Omega \ @ \ V_{\rm GS} = 2.7 \ V. \\ \end{tabular}$
- Very low level gate drive requirements allowing direct operation in 3 V circuits (V_{GS(th)} < 1.5 V).
- Gate-Source Zener for ESD ruggedness (>6kV Human Body Model).
- Compact industry standard SC70-6 surface mount package.







^{*} The pinouts are symmetrical; pin 1 and 4 are interchangeable.

Units inside the carrier can be of either orientation and will not affect the functionality of the device.

Absolute Maximum Ratings T. = 25°C unless otherwise noted

| Symbol | Parameter | FDG6303N | Units | |
|-------------------|--|------------|----------|--|
| V _{DSS} | Drain-Source Voltage | 25 | V | |
| V_{GSS} | Gate-Source Voltage | 8 | V | |
| l _D | Drain/Output Current - Continuous | 0.5 | А | |
| | - Pulsed | 1.5 | | |
|) | Maximum Power Dissipation (Note 1) | 0.3 | W | |
| T_J , T_{STG} | Operating and Storage Temperature Range | -55 to 150 | ℃ | |
| ESD | Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100 pF / 1500 Ω) | 6.0 | kV | |
| THERMA | L CHARACTERISTICS | | <u>.</u> | |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | 415 | °C/W | |

| Symbol | Parameter | Conditions | Min | Тур | Max | Units |
|----------------------------------|---|---|------|------|------|-------|
| OFF CHAR | ACTERISTICS | • | | | | • |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$ | 25 | | | V |
| $\Delta BV_{DSS}/\Delta T_{J}$ | Breakdown Voltage Temp. Coefficient | I _D = 250 μA, Referenced to 25°C | | 26 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | | | 1 | μA | |
| | | T _J = 55°C | | | 10 | μA |
| GSS | Gate - Body Leakage Current | V _{GS} = 8 V, V _{DS} = 0 V | | | 100 | nA |
| | CTERISTICS (Note 2) | | 1 | ı | | 1 |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | 0.65 | 0.8 | 1.5 | V |
| $\Delta V_{GS(th)}/\Delta T_{J}$ | Gate Threshold Voltage Temp.Coefficient | I _D = 250 μA, Referenced to 25°C | | -2.6 | | mV/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance | $V_{GS} = 4.5 \text{ V}, I_{D} = 0.5 \text{ A}$ | | 0.34 | 0.45 | Ω |
| , | | T _J =125°C | | 0.55 | 0.77 | |
| | | $V_{GS} = 2.7 \text{ V}, I_D = 0.2 \text{ A}$ | | 0.44 | 0.6 | |
| D(ON) | On-State Drain Current | $V_{GS} = 2.7 \text{ V}, \ V_{DS} = 5 \text{ V}$ | 0.5 | | | Α |
| g _{FS} | Forward Transconductance | $V_{DS} = 5 \text{ V}, I_{D} = 0.5 \text{ A}$ | | 1.45 | | S |
| DYNAMIC C | HARACTERISTICS | · | | | | • |
| C _{iss} | Input Capacitance | | 50 | | pF | |
| Coss | Output Capacitance | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz | | 28 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 9 | | pF |
| SWITCHING | CHARACTERISTICS (Note 2) | | | | | |
| D(on) | Turn - On Delay Time | , DD . D . | | | 6 | ns |
| т | Turn - On Rise Time | $V_{GS} = 4.5 \text{ V}, R_{GEN} = 50 \Omega$ | | 8.5 | 18 | ns |
| D(off) | Turn - Off Delay Time | | | 17 | 30 | ns |
| f | Turn - Off Fall Time | | | 13 | 25 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 5 \text{ V}, I_{D} = 0.5 \text{ A}, V_{GS} = 4.5 \text{ V}$ | | 1.64 | 2.3 | nC |
| Q_{gs} | Gate-Source Charge | $V_{GS} = 4.5 \text{ V}$ | | 0.38 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 0.45 | | nC |
| DRAIN-SOU | RCE DIODE CHARACTERISTICS AND MAXIN | IUM RATINGS | | | | |
| s | Maximum Continuous Source Current | | | | 0.25 | А |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = 0.25 \text{ A (Note 2)}$ | | 0.8 | 1.2 | V |

Notes:

1. R_{g,x} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{g,x} is guaranteed by design while R_{gcA} is determined by the user's board design. $R_{guA} = 415^{\circ}$ C/W on minimum pad mounting on FR-4 board in still air. 2. Pulse Test: Pulse Width $\leq 300\mu$ s, Duty Cycle $\leq 2.0\%$.

Typical Electrical Characteristics

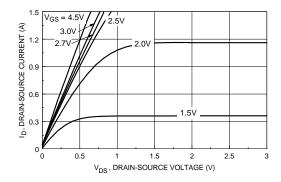


Figure 1. On-Region Characteristics.

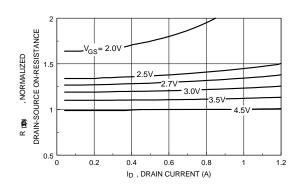


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

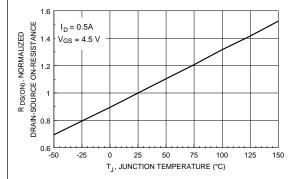


Figure 3. On-Resistance Variation with Temperature.

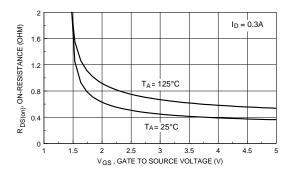


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

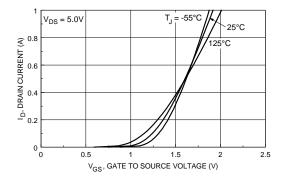


Figure 5. Transfer Characteristics.

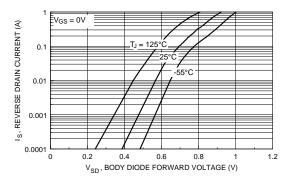


Figure 6 . Body Diode Forward Voltage
Variation with Source Current
and Temperature.

Typical Electrical Characteristics (continued)

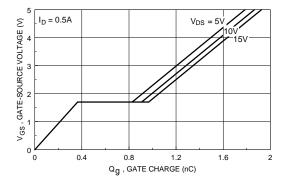


Figure 7. Gate Charge Characteristics.

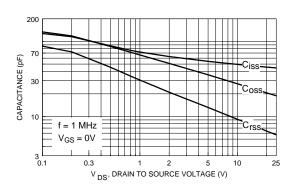


Figure 8. Capacitance Characteristics.

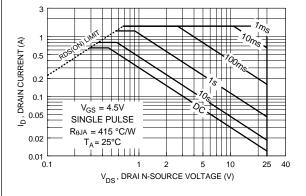


Figure 9. Maximum Safe Operating Area.

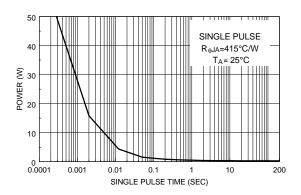


Figure 10. Single Pulse Maximum Power Dissipation.

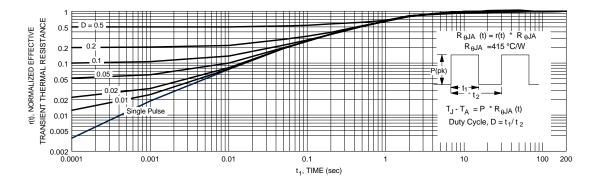
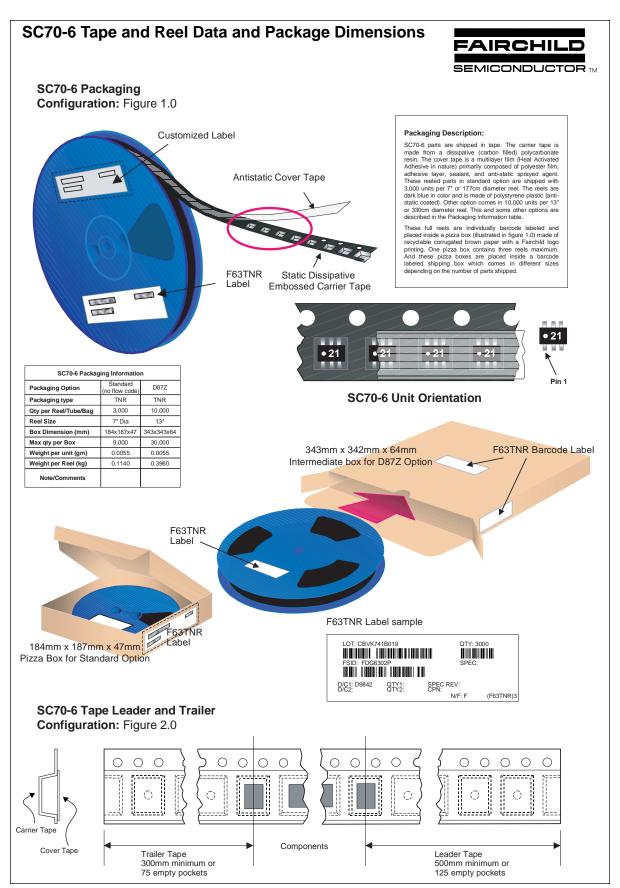


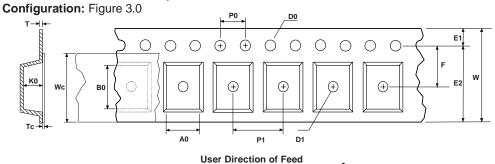
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1. Transient thermal response will change depending on the circuit board design.





SC70-6 Embossed Carrier Tape

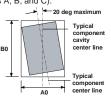


| Dimensions are in millimeter | | | | | | | | | | | | | | |
|------------------------------|-----------------|-----------------|---------------|-----------------|-------------------|-----------------|-------------|-----------------|---------------|---------------|-----------------|-------------------|---------------|-----------------|
| Pkg type | A0 | В0 | w | D0 | D1 | E1 | E2 | F | P1 | P0 | K0 | т | Wc | Тс |
| SC70-6 (8mm) | 2.24 +/-0.10 | 2.34 +/-0.10 | 8.0 +/-0.3 | 1.55 +/-0.05 | 1.125 +/-0.125 | 1.75 +/-0.10 | 6.25 min | 3.50 +/-0.05 | 4.0 +/-0.1 | 4.0 +/-0.1 | 1.20 +/-0.10 | 0.255 +/-0.150 | 5.2 +/-0.3 | 0.06 +/-0.02 |

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

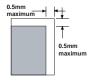


Sketch A (Side or Front Sectional View)
Component Rotation



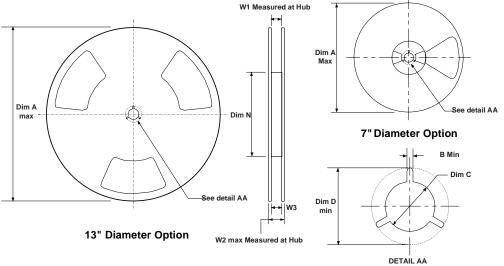
Sketch B (Top View)

Component Rotation



Sketch C (Top View)
Component lateral movement

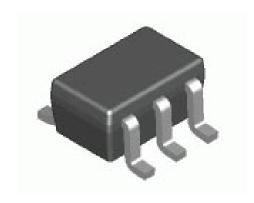
SC70-6 Reel Configuration: Figure 4.0

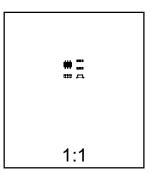


| Dimensions are in inches and millimeters | | | | | | | | | |
|--|----------------|---------------|--------------|-------------------------------------|---------------|-------------|-----------------------------------|---------------|-----------------------------|
| Tape Size | Reel Option | Dim A | Dim B | Dim C | Dim D | Dim N | Dim W1 | Dim W2 | Dim W3 (LSL-USL) |
| 8mm | 7" Dia | 7.00 177.8 | 0.059 1.5 | 0.512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 2.165 55 | 0.331 +0.059/-0.000 8.4 +1.5/0 | 0.567 14.4 | 0.311 - 0.429 7.9 - 10.9 |
| 8mm | 13" Dia | 13.00 330 | 0.059 1.5 | 0.512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 4.00 100 | 0.331 +0.059/-0.000 8.4 +1.5/0 | 0.567 14.4 | 0.311 - 0.429 7.9 - 10.9 |

SC70-6 Tape and Reel Data and Package Dimensions, continued

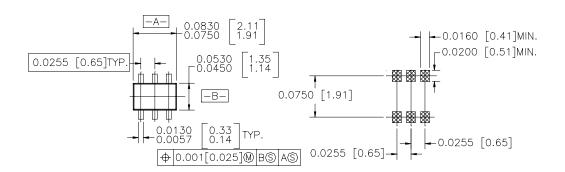
SC70-6 (FS PKG Code 76)



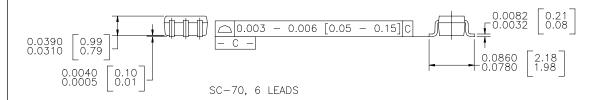


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0055



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